

### IN THE CLAIMS

Please amend the claims as follows:

Claims 1-17 (Canceled).

Claim 18 (New): A process for manufacturing an anisotropic conducting film comprising a layer of electrically insulating material and conducting through inserts, said process comprising:

a) forming on a substrate of at least one layer of material with through holes, the said layer being called the perforated layer,

b) filling of the through holes to form conducting inserts;

and further comprising producing a mask partially covering a first end of the conducting inserts and etching of the unmasked part of the ends of the conducting inserts so as to obtain conducting inserts with pointed ends.

Claim 19 (New): The process according to claim 18, wherein the filling step b) is done by electrolysis, step a) comprises deposition of a conducting layer on the substrate before formation of the perforated layer, this layer being etched after the conducting inserts are made.

Claim 20 (New): The process according to claim 18, wherein the perforated layer in step a) is done by depositing a layer of photosensitive resin, insolation of this resin through a mask and development of this resin to obtain the through holes.

Claim 21 (New): The process according to claim 18, wherein the perforated layer in step a) is removed after the filling step b) and a step to deposit an insulating layer is performed on the substrate to form the insulating layer of the anisotropic conducting film.

Claim 22 (New): The process according to claim 18, wherein a passivation layer covers the substrate in which at least one contact pad is housed.

Claim 23 (New): The process according to claim 18, wherein production of the mask partially covering one end of the conducting inserts and etching of the unmasked part comprises:

- depositing a photosensitive resin on the perforated layer in which the conducting inserts are formed,
- insulating and developing the photosensitive resin through the mask such that only a disk of resin remains at the top of a first end of each conducting insert,
- isotropic chemical etching of the first ends of the conducting inserts until the resin disks are removed such that a point appears at the end of each conducting insert.

Claim 24 (New): The process according to claim 18, wherein production of the mask partially covering one end of the conducting inserts and etching of the unmasked part comprises:

- coating of a buffer substrate (A) by a material that can be transferred and that will protect the end of the conducting inserts,
- transferring said material onto the conducting inserts such that only a disk of material remains at the top of the first end of each conducting insert,

- isotropic chemical etching of the first ends of the conducting inserts until the material disks are removed such that a point appears on the first end of each conducting insert.

Claim 25 (New): The process according to claim 24, wherein the step in which the through holes are filled is done such that the first end of each conducting insert is in the form of a nail head.

Claim 26 (New): The process according to claim 18, wherein after the first pointed ends of the conducting inserts have been made, a protection layer is formed on the points of the conducting inserts.

Claim 27 (New): The process according to claim 26, wherein the protection layer is advantageously an anti-oxidising layer.

Claim 28 (New): The process according to claim 27, wherein the anti-oxidising layer is gold plating prepared by at least one technique selected from the group consisting of electroless plating, electrolysis and spraying of gold.

Claim 29 (New): The process according to claim 24, wherein the transfer of the transferable material designed to protect the end of the conducting inserts is a polymer with better adhesive properties on the conducting inserts than on the buffer substrate (A) on which the material is located before the transfer.

Claim 30 (New): The process according to claim 24, wherein the transfer of the transferable material designed to protect the end of the conducting inserts is a resin with better adhesive properties on the conducting inserts than on the buffer substrate (A) on which the material is located before the transfer.

Claim 31 (New): The process according to claim 24, wherein the material that can be transferred onto the end of the conducting inserts is transferred by applying pressure on the buffer substrate (A) on which the material is located before the transfer.

Claim 32 (New): The process according to claim 18, wherein the through holes are filled utilizing at least one technique selected from the group consisting of an auto catalytic deposition, electrolytic growth, chemical deposition, physical deposition and impregnation.

Claim 33 (New): The process according to claim 18, wherein prior to manufacturing of the film, one or several layers are deposited on the substrate that make it possible to separate the film from the substrate after the film has been obtained, and to make the assembly mechanically stiff.

Claim 34 (New): A process for manufacturing a semiconducting chip, wherein the process includes a process for manufacturing an anisotropic conducting film according to claim 18, said film being placed on a semiconducting wafer, and a step to cut out the structure thus obtained.